



Atty. Dkt. No. 017447/0170

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant: Koichi WATANABE et al.

Title: SPUTTERING TARGET

Appl. No.: 09/720,730

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Examiner: S. IP

Art Unit: 1742

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MP  
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**AMENDMENT AND RESPONSE UNDER**

**37 CFR 1.111**

Commissioner for Patents  
Washington, D.C. 20231

**RECEIVED**  
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Sir:

In response to the Office Action dated March 28, 2002, in the above-identified application, Applicants respectfully request that the following amendments be entered into the application:

**IN THE SPECIFICATION**

Please substitute the following portions of the specification:

Page 4, lines 7-11:

31  
A first sputtering target of the present invention is characterized in consisting essentially of high purity Nb of which Ta content is 3000 ppm or less. The first sputtering target is further characterized in that the dispersion of the Ta content in the target is within 30%.

Page 4, lines 12-19:

32  
A second sputtering target of the present invention is characterized in consisting essentially of high purity Nb wherein each grain of the Nb has a grain diameter in the